





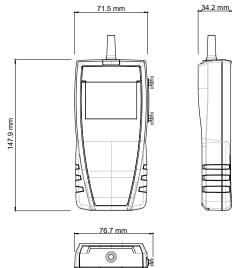
Technical specifications

Parameters	Measuring units	Accuray ⁽¹⁾	Measuring range	Resolution
Relative humidity	%RH	Accuracy* (Repetability, linearity, hysteresis): ±1.8% RH (from 15 °C to 25 °C) Factory calibration uncertainty: ±0.88% RH Drift linked to the temperature: ±0.04 x (T-20) %RH (if T < 15 °C or T > 25 °C)	From 5 to 95 %RH	0.1 % RH
Dew point	$^{\circ}C_{td'} ^{\circ}F_{td}$	$\pm 0.8\%$ of reading $\pm 0.6~^{\circ}\mathrm{C}_{_{td}}$	From -40 to +70 $^{\circ}C_{td}$	0.1 °C _{td}
Ambient temperature	°C, °F	$\pm 0.4\%$ of reading ± 0.3 °C	From -20 to +70 °C	0.1 °C

General features

Measuring element	Digital sensor (CMOS)
Display	4 lines, LCD technology. Dimensions 50 x 36 mm 2 lines of 5 digits with 7 segments (value) 2 lines of 5 digits with 16 segments (units)
Cable	Coiled, 0.45 m length, expanding to 2.4 m
Housing	ABS, protection IP54
Keypad	5 keys
European directives	2014/30/EU EMC; 2014/35/EU Low Voltage; 2011/65/EU RoHS II; 2012/19/EU WEEE
Power supply	4 batteries AAA LR03 1.5 V
Battery life	150 hours
Ambience	Neutral gas
Conditions of use (°C, %RH, m)	From -10 to +50 °C. In non condensing conditions. From 0 to 2000 m.
Operating temperature (probe)	From -20 to +70 °C
Storage temperature	From -20 to +80 °C
Auto shut-off	Adjustable from 0 to 120 min
Weight	310 g

Dimensions (in mm)



Kit content

- Hygrometry probe Ø 13 mm, 110 mm length
- Calibration certificate
- Transport case (ref.: ST 110)

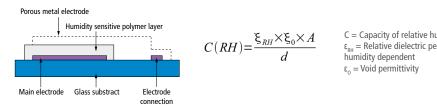
Accessories

Reference
CQ 15
RTE
MT 51

Operating principle

Measurement of capacitive hygrometry

On the capacitive probes, a sensitive polymer layer reacts with the humidity present between two metal layers which cover a glass substract. Water absorption is a function of relative humidity of the surrounding environment, and modifies the dielectric constant. The measured signal is directly proportional to the relative humidity and independent on the ambient pressure.



 $\mathsf{C}=\mathsf{Capacity}$ of relative humidity sensor $\epsilon_{_{RH}} =$ Relative dielectric permittivity,

A = Electrodes area d = Electrodes spacing HR = Relative humidity

Semiconductor temperature sensor

The direct tension of a silicon diode is dependent on the temperature, in accordance with the following equation:

$$V_{BE} = V_{G0}(1 - T/T_0) + V_{BE0}(T/T_0) + (nKT/q)\ln(T_0/T) + (KT/q)\ln(IC/IC_0)$$

T = Temperature in Kelvin $V_{\rm _{G0}}$ = Voltage of the band gap at the absolute zero $V_{BE0} =$ Voltage of the band gap at T₀ and IC₀

- K = Boltzmann constant q = charge of an electron
- $n = Dependent \ constant \ of \ the \ instrument$

Warranty

Instruments have 1-year guarantee for any manufacturing defect (return to our After-Sales Service required for appraisal).

Maintenance

We carry out calibration, adjustment and maintenance of your instruments to guarantee a constant level of quality of your measurements. As part of Quality Assurance Standards, we recommend you to carry out a yearly checking.

FT_EN – HD110 – 10/11/17 – Non-contractual document – We reserve the right to modify the characteristics of our products without prior notice.